Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	301402	(kozo near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 kotooka or yoshiyuki near2 shimanuki).in. or (KOMATSU DENSHI KINZOKU KABUSHIKI KAISHA).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:02
L4	45	1 and heat near4 treat$5 near10 temperature same initiat$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:03
L3	0	1 and heat near4 treat$5 near10 temperature same initat$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:03
L2	4178	1 and heat near4 treat$5 near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:03
L6	524	1 and heat near4 treat$5 near10 temperature same (silicon or si) near5 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:04
L5	2	1 and heat near4 treat$5 near10 temperature same initiat$5 same (silicon or si) near5 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:04
L8	11	1 and heat near4 treat$5 near10 temperature same (silicon or si) near5 (substrate or wafer) and (ramp$5 or elevat$4 or rais$4) near10 temperature.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:06
L7	127	1 and heat near4 treat$5 near10 temperature same (silicon or si) near5 (substrate or wafer) and (ramp$5 or elevat$4 or rais$4) near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:07
L9	51	1 and heat near4 treat$5 near10 temperature same (silicon or si) near5 (substrate or wafer) and (ramp$5 or elevat$4 or rais$4) near10 temperature and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:08

L10	121	heat near2 treat$4 near10 temperature near10 (ramp$4 or rate) same (si or silicon) near5 (single near2 crystal$5 or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:09
S67	113	heat near2 treat$4 near10 temperature near10 (ramp$4 or rate) same (si or silicon) near5 (single near2 crystal$5 or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34
S48	44	(anneal$ or heat$3 near2 treat$4 or rta or rtp or ptp) same (Si or silicon) near4 wafer same (low or slow or reduc$4) near2 rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34
S15	82	wafer and (anneal$3 or (heat adj treat$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and (oxygen or O2) and (oSF or OSIF or BMD or (oxide adj induced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34
L13	184	wafer and (anneal$3 or (heat adj treat$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and (oxygen or O2) and (oSF or OSIF or BMD or (oxide adj induced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34
L12	121	heat near2 treat$4 near10 temperature near10 (ramp$4 or rate) same (si or silicon) near5 (single near2 crystal$5 or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34
L11	50	(anneal$ or heat$3 near2 treat$4 or rta or rtp or ptp) same (Si or silicon) near4 wafer same (low or slow or reduc$4) near2 rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:34